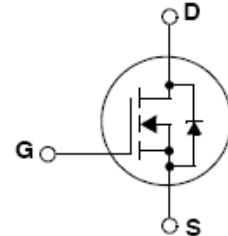




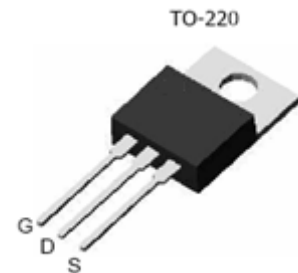
General Description

This Power MOSFET device has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.



Features

- $V_{DS} = 75\text{ V}$
- $I_D = 80\text{ A}$
- Typical $R_{DS(ON)} = 7.5\text{ m}\Omega$ ($V_{GS} = 10\text{ V}, I_D = 40\text{ A}$)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	75	V
I_D	Drain Current(continuous)at $T_c = 25^\circ\text{C}$	80	A
I_{DM}	Drain Current (pulsed) (Note1)	320	A
V_{GS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Note2)	800	mJ
I_{AR}	Avalanche Current (Note1)	35	A
E_{AR}	Repetitive Avalanche Energy (Note1)	18	mJ
dv/dt	Peak Diode Recovery dv/dt (Note3)	11	V/ns
P_D	Power Dissipation ($T_c = 25^\circ\text{C}$)	210	W
T_J, T_{stg}	Operating junction and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose	300	$^\circ\text{C}$



Ordering Information

Part Number	Package	Packaging
BF975NF75B	TO-220	Tube

Thermal Data

Symbol	Parameter	Max.	Unit
Rthj-Case	Thermal Resistance Junction-Case	0.6	°C/W
Rthj-Amb	Thermal Resistance Junction-Ambient	63.0	°C/W

Electrical Characteristics(T_c = 25°C)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D =250uA, V _{GS} =0V	75			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =75V, V _{GS} =0V, T _c =25°C			1	uA
		V _{DS} =75V, V _{GS} =0V, T _c =125°C			10	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2		4	V
R _{DS(on)}	Static Drain-Source On Resistance	V _{GS} =10V, I _D =40A		7.5	10	mΩ
C _{iss}	Input Capacitance	V _{DS} =20V, f=1MHZ, V _{GS} =0V		3839		pF
C _{oss}	Output Capacitance			328		pF
C _{rss}	Reverse Transfer Capacitance			33.6		pF
t _{d(on)}	Turn-On Delay Time	V _{DD} =37.5V, R _L =15Ω V _{GS} =10V, R _G =10Ω (Note4, 5)		32		ns
t _r	Rise Time			29		ns
t _{d(off)}	Turn-Off Delay Time			110		ns
t _f	Fall Time			23		ns
Q _g	Total Gate Charge				118	
Q _{gs}	Gate-Source Charge	V _{DD} =60V, I _D =80A V _{GS} =10V (Note4, 5)		50		nC
Q _{gd}	Gate-Drain Charge			35		nC
V _{SD} (*)	Forward On Voltage	I _{SD} =25A, V _{GS} =0V			1.5	V
T _{rr}	Reverse Recovery Time	V _{DD} =37.5V, I _F =80A, di/dt=100A/us (Note4)		70		ns

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
 2. V_{DD} = 37.5V, R_G = 25 Ω, Starting T_J = 25°C
 3. I_{SD} ≤ 80A, di/dt ≤ 280A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
 4. Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 2%
 5. Essentially independent of operating temperature
- (*)Pulsed:Pulse duration

Typical characteristics (25°C unless noted)

Figure 1 Output Characteristics

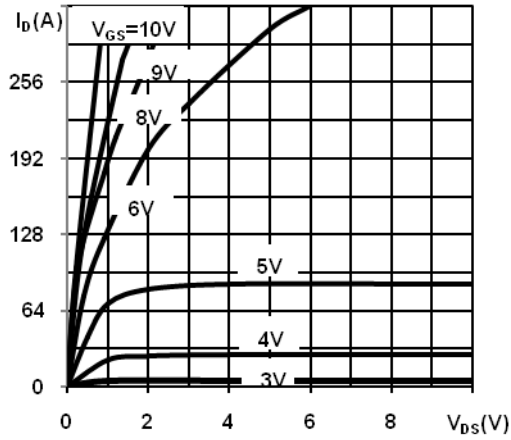


Figure 2 Transfer Characteristics

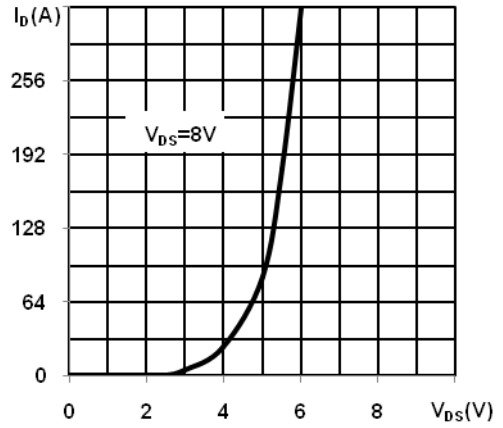


Figure 3 Normalized Threshold Voltage vs. Temperature

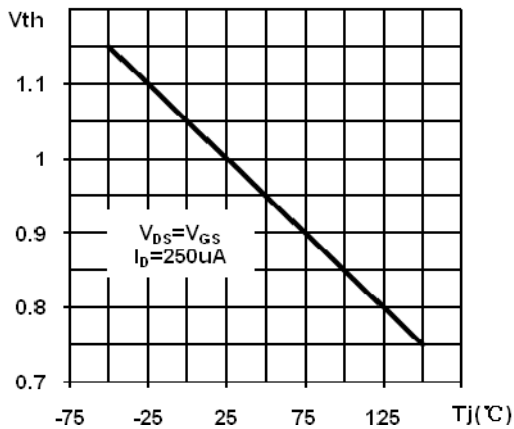


Figure 4 Normalized BV_{DSS} vs. Temperature

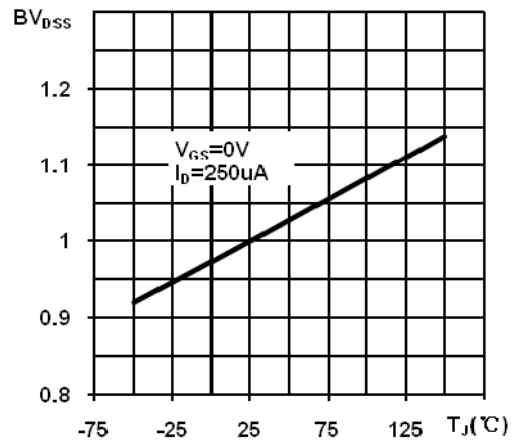


Figure 5 Normalized on Resistance vs Temperature

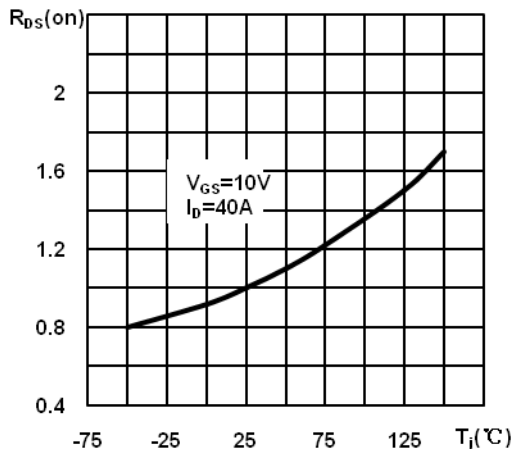


Figure 6 Source-Drain Diode Forward Characteristics

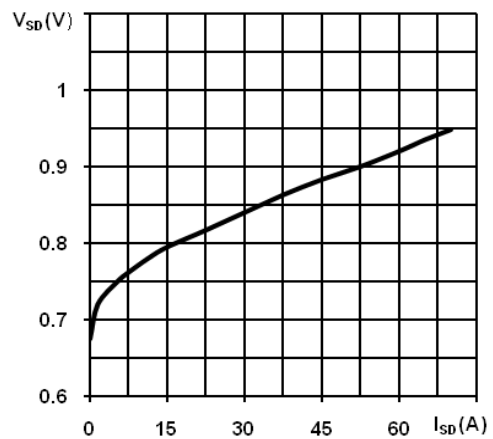


Figure 7 Capacitance

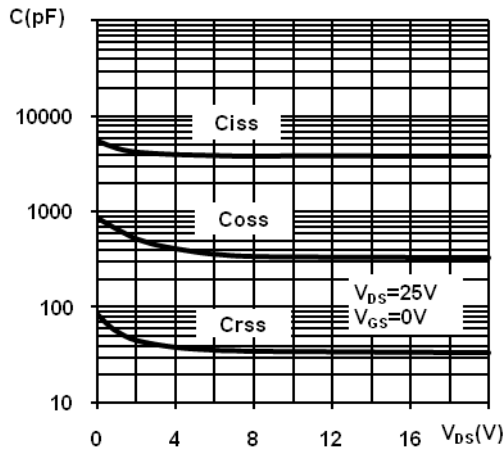


Figure 8 Gate Charge

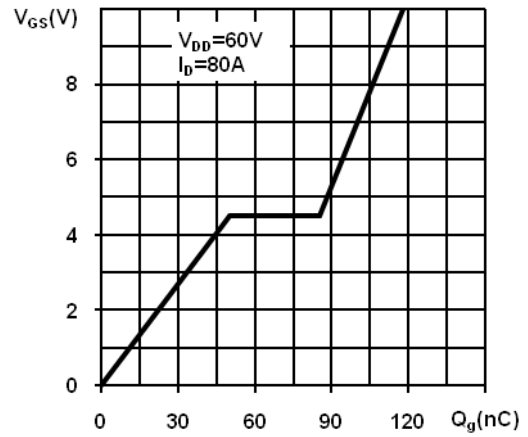


Figure 9 Safe Operating Area

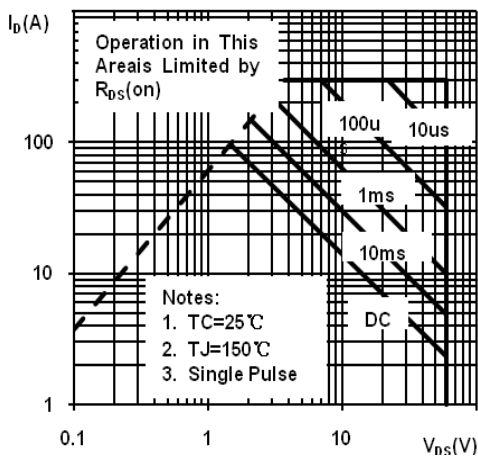


Figure 10 Maximum Drain Current vs Case Temperature

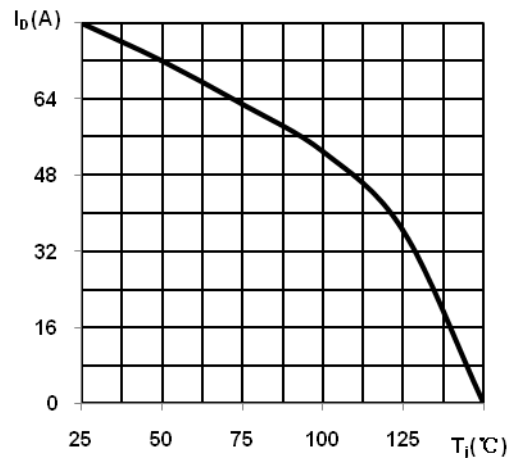
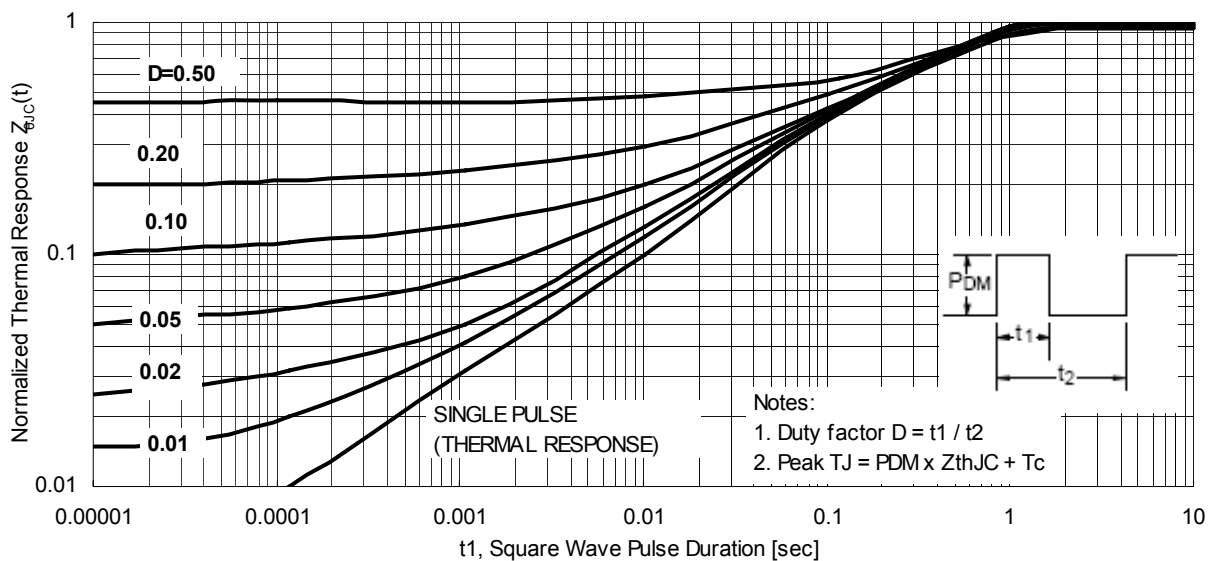
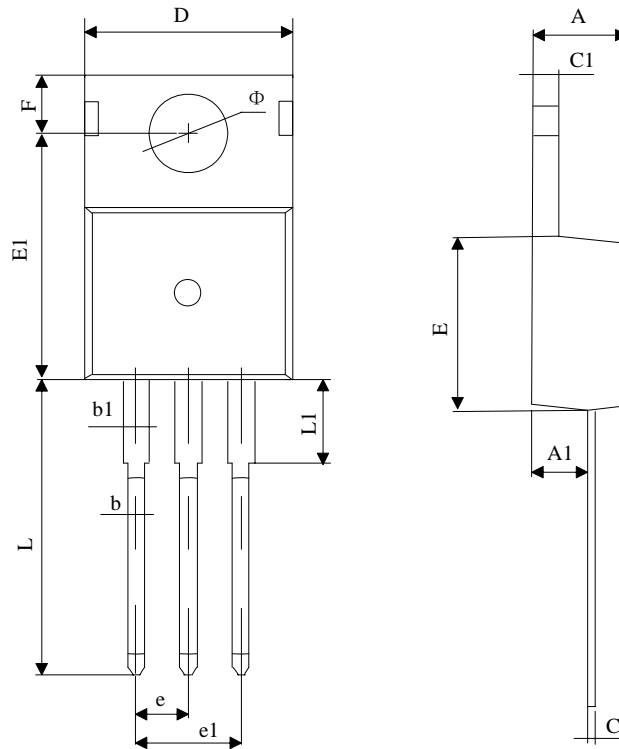


Figure 11 Normalized Maximum Transient Thermal Impedance



Package Drawing



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.45	4.55	0.175	0.179
A1	2.38	2.42	0.093	0.095
b	0.70	0.90	0.028	0.035
b1	1.42	1.62	0.056	0.064
c	0.45	0.55	0.018	0.022
c1	1.25	1.35	0.049	0.053
D	9.85	9.95	0.388	0.392
E	9.11	9.29	0.359	0.366
E1	12.85	12.95	0.506	0.510
e	2.540TYP		0.100TYP	
e1	5.04	5.12	0.198	0.202
F	2.77	2.83	0.109	0.111
L	12.98	13.18	0.511	0.519
L1	2.97	3.03	0.117	0.119
Φ	3.58	3.62	0.141	0.143



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